Abstract of the Disclosure:

A reflection mask for projecting a structure onto a semiconductor wafer contains a carrier material, a layer stack for reflecting obliquely incident light and formed of an alternating sequence of reflective layers disposed on a front side of the carrier material, and a light-absorbing layer. In the light-absorbing layer at least one opening is formed as the structure to be projected and which is disposed on the alternating layer stack. An electrically conductive layer is buried within the carrier material near a surface of a rear side of the carrier material. The buried electrically conductive layer is produced by ion implantation preferably in a whole-area manner on the rear side of the mask. The depth and the depth extent of the layer are controlled by the ion energy and also the dose.

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